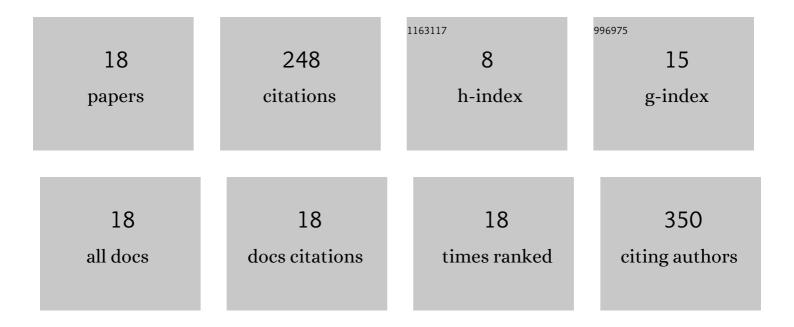
## **Dimitrios Velessiotis**

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Vertical devices of self-assembled hybrid organic/inorganic monolayers based on tungsten polyoxometalates. Microelectronic Engineering, 2008, 85, 1399-1402.	2.4	54
2	Tunneling transport in polyoxometalate based composite materials. Applied Physics Letters, 2003, 83, 488-490.	3.3	47
3	Molecular Storage Elements for Proton Memory Devices. Advanced Materials, 2008, 20, 4568-4574.	21.0	36
4	Development mechanism study by dissolution monitoring of positive methacrylate photoresists. Microelectronic Engineering, 2000, 53, 489-492.	2.4	25
5	Tungstate polyoxometalates as active components of molecular devices. Journal of Applied Physics, 2005, 98, 084503.	2.5	22
6	Molecular junctions made of tungsten-polyoxometalate self-assembled monolayers: Towards polyoxometalate-based molecular electronics devices. Microelectronic Engineering, 2011, 88, 2775-2777.	2.4	17
7	Aqueous base development and acid diffusion length optimization in negative epoxy resist for electron beam lithography. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 3431.	1.6	9
8	Transport properties of polyoxometalate containing polymeric materials. Synthetic Metals, 2003, 138, 267-269.	3.9	8
9	Hybrid organic–inorganic materials for molecular proton memory devices. Organic Electronics, 2009, 10, 711-718.	2.6	8
10	Emergence of ambient temperature ferroelectricity in <i>meso</i> -tetrakis(1-methylpyridinium-4-yl)porphyrin chloride thin films. Applied Physics Letters, 2013, 103, 022908.	3.3	5
11	Phosphorous Diffusion in N2+-Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. ECS Journal of Solid State Science and Technology, 2017, 6, P418-P428.	1.8	5
12	Application of the partial wave expansion method in 3-D low energy electron beam lithography simulation. Microelectronic Engineering, 2001, 57-58, 297-302.	2.4	4
13	(Invited) Issues with n-type Dopants in Germanium. ECS Transactions, 2018, 86, 51-58.	0.5	4
14	Molecular nanodevices based on functionalized cyclodextrins. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2532-2535.	1.8	2
15	Conduction mechanisms in tungsten-polyoxometalate self-assembled molecular junctions. Microelectronic Engineering, 2012, 97, 150-153.	2.4	2
16	Compound polymeric materials in molecular nanodevices: electrical behavior of zero-dimension semiconducting inorganic molecules embedded in a polymer substrate. Journal of Physics: Conference Series, 2005, 10, 93-96.	0.4	0
17	Substrate damage in ion-implanted (100) germanium after extended ms flash lamp annealing: Origins and suppression. Materials Science in Semiconductor Processing, 2021, 122, 105477.	4.0	0
18	Post-metallization annealing and photolithography effects in p-type Ge/Al2O3/Al MOS structures. ECS Journal of Solid State Science and Technology, 0, , .	1.8	0